

SANYO	No.3467	2SK1464
		N-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON-state resistance.
- Very high-speed switching.
- Converters.

Absolute Maximum Ratings at Ta = 25°C

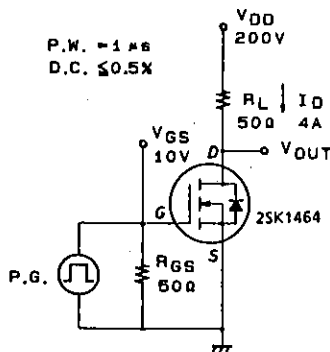
Drain to Source Voltage	V_{DS}	900		unit
Gate to Source Voltage	V_{GS}	±30		V
Drain Current(DC)	I_D	8		A
Drain Current(Pulse)	I_{DP}	16	PW ≤ 10μs, duty cycle ≤ 1%	A
Allowable Power Dissipation	P_D	80	Tc = 25°C	W
		3.0		W
Channel Temperature	T_{ch}	150		°C
Storage Temperature	T_{stg}	-55 to +150		°C

Electrical Characteristics at Ta = 25°C

		min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$ $I_D = 1mA, V_{GS} = 0$	900			V
Zero Gate Voltage Drain Current	I_{DSS} $V_{DS} = 900V, V_{GS} = 0$			1.0	mA
Gate to Source Leakage Current	I_{GSS} $V_{GS} = \pm 30V, V_{DS} = 0$			±100	nA
Cutoff Voltage	$V_{GS(off)}$ $V_{DS} = 10V, I_D = 1mA$	2.0		3.0	V
Forward Transfer Admittance	$ Y_{fs} $ $V_{DS} = 20V, I_D = 4A$	2.5	5.0		S
Static Drain to Source on State Resistance	$R_{DS(on)}$ $I_D = 4A, V_{GS} = 10V$		1.2	1.6	Ω
Input Capacitance	C_{iss} $V_{DS} = 20V, f = 1MHz$		1600		pF
Output Capacitance	C_{oss} $V_{DS} = 20V, f = 1MHz$		500		pF
Reverse Transfer Capacitance	C_{rss} $V_{DS} = 20V, f = 1MHz$		350		pF
Turn-ON Delay Time	$t_{d(on)}$		20		ns
Rise Time	t_r	$I_D = 4A, V_{GS} = 10V$ $V_{DD} = 200V, R_{GS} = 50\Omega$		80	ns
Turn-OFF Delay Time	$t_{d(off)}$			350	ns
Fall Time	t_f		150		ns
Diode Forward Voltage	V_{SD} $I_S = 8A, V_{GS} = 0$			1.8	V

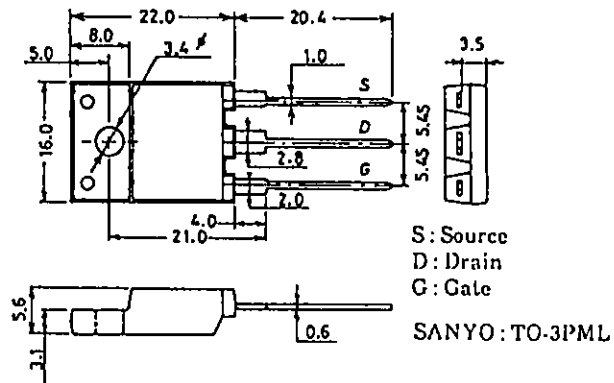
(Note) Be careful in handling the 2SK1464 because it has no protection diode between gate and source.

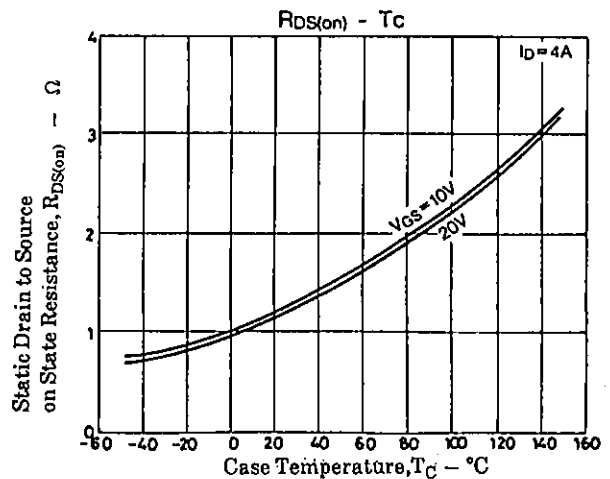
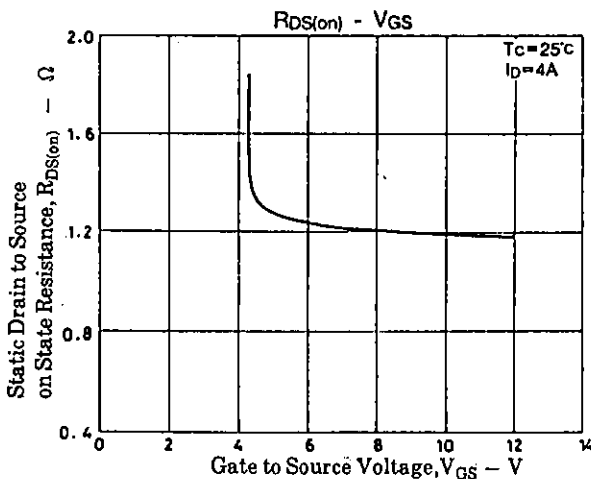
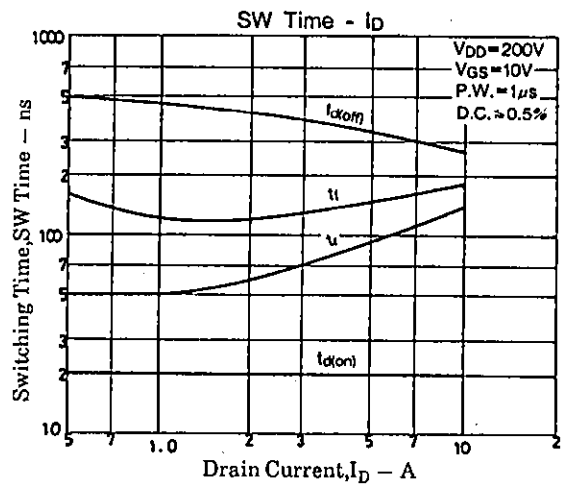
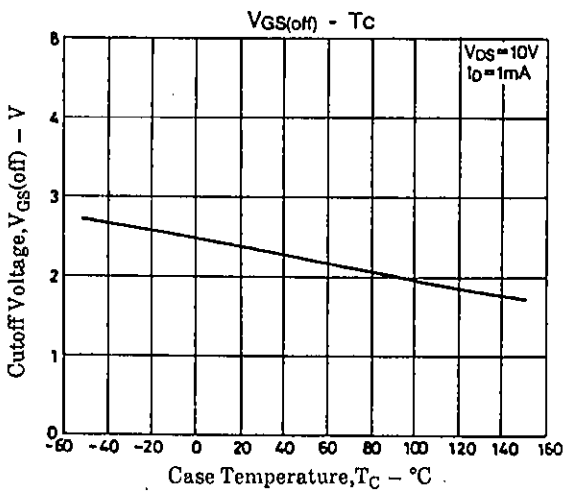
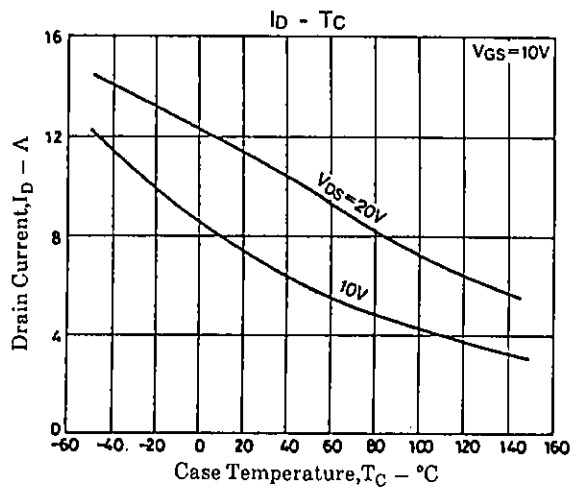
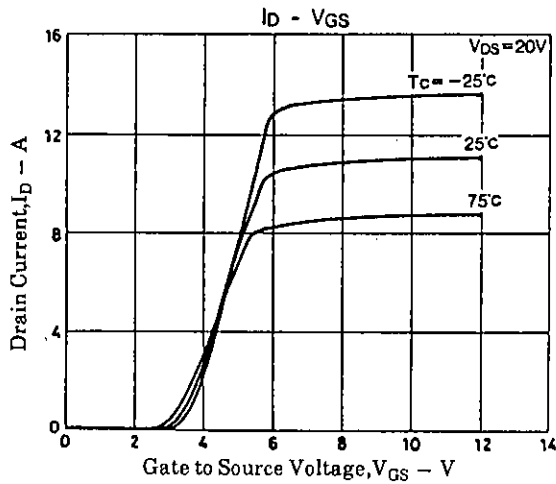
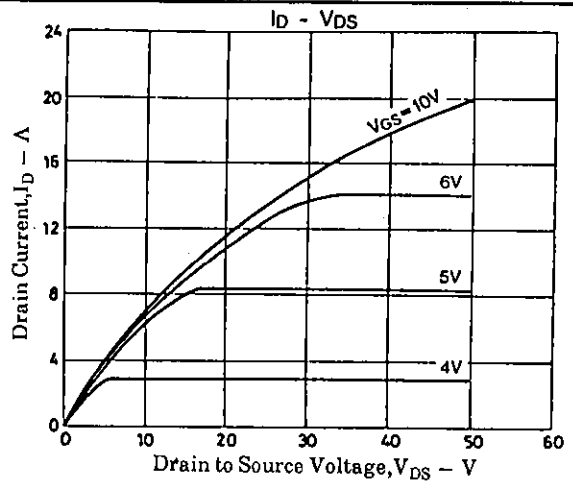
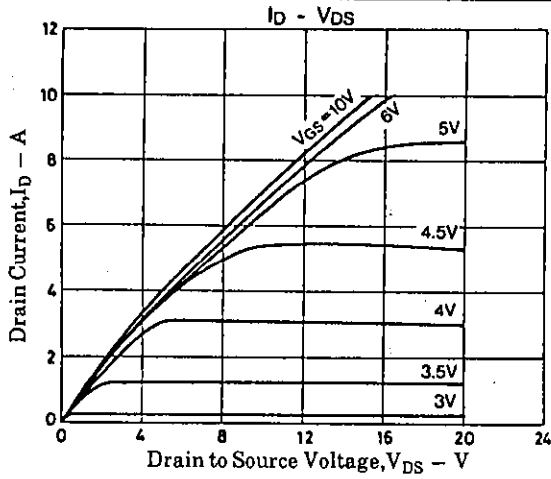
Switching Time Test Circuit

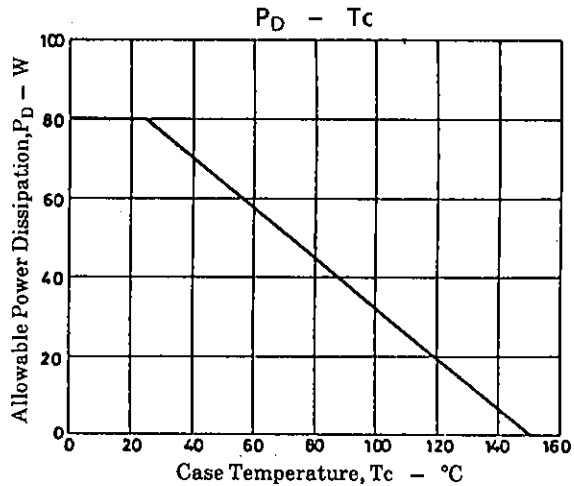
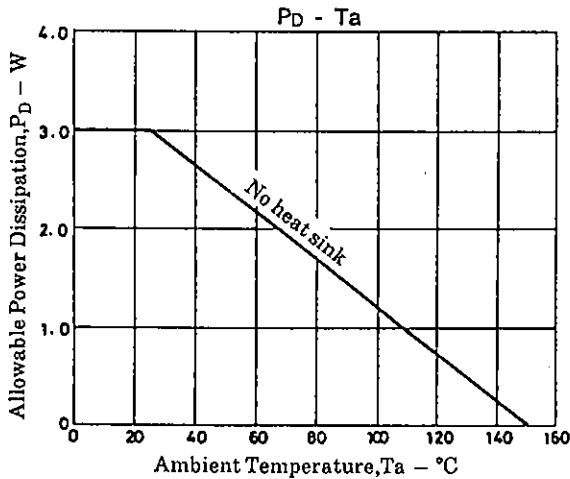
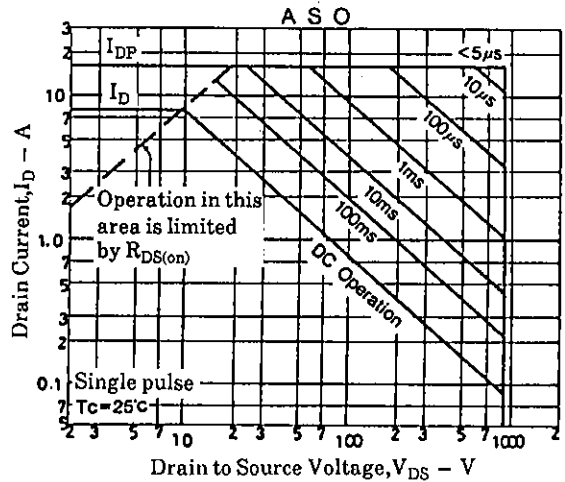
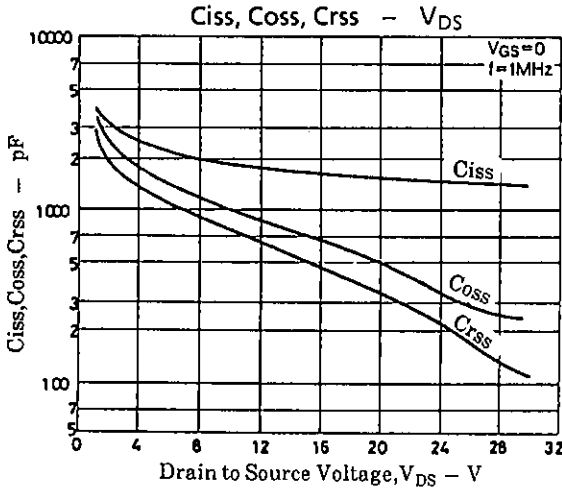
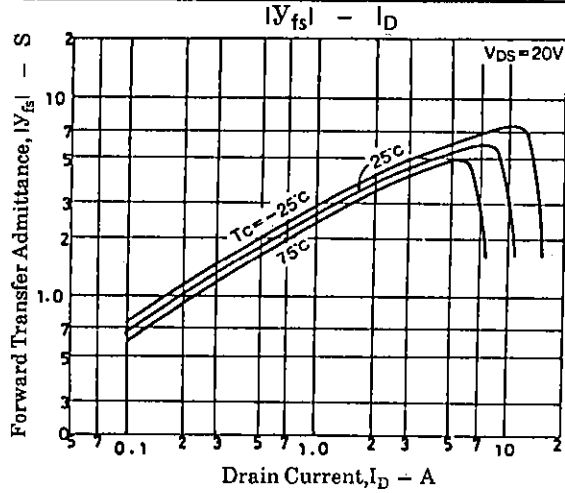
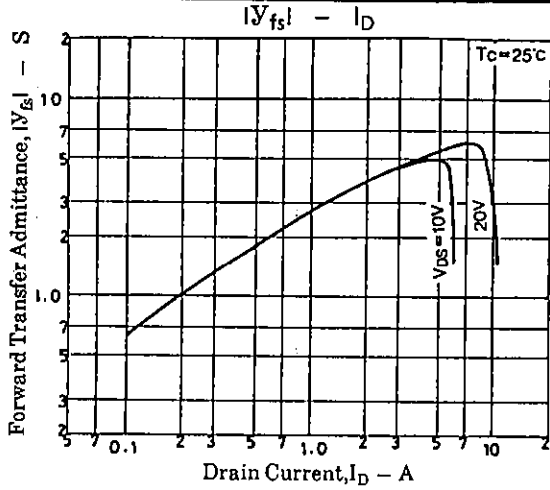


Package Dimensions 2076

(unit : mm)







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